

BD137

1.5 A, 60 V NPN Power Bipolar Junction Transistor

Product Overview

For complete documentation, see the data sheet.

This series of plastic, medium-power NPN power bipolar junction transistors are designed for use as audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

Features

- Minimum DC Current Gain hFE = 40 @ IC = 0.15 A
- BD135, BD137, BD139 are complementary with BD136, BD138, BD140
- These are Pb-Free Devices

Part Electrical Specifications																	
Product	Pricing (\$/Unit)	Complian ce	Stat	Pola rity	Тур	V _{CE(s} at) Max (V)	I _C Con t. (A)	V _{CEO} Min (V)	V _{CBO} (V)	V _{EBO} (V)	V _{BE(s} at) (V)	V _{BE(on)} (V)	h _{FE} Min	h _{FE} Max	f _T Min (MH z)	P _{TM} Max (W)	Pac kag e Typ e
BD137G	0.2883	РЬ (Н	Acti ve	NPN	Gen eral Pur pos e	0.5	1.5	60	60	5	-	1	40	250	-	12.5	TO- 225 -3